

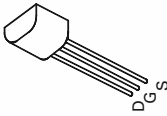
P-CHANNEL ENHANCEMENT
MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 400 Volt V_{DS}
- * $R_{DS(on)}=150\Omega$

ZVP0540A



E-Line
TO92 Compatible

查询ZVP0540A供应商

捷多邦，专业PCB打样工厂，24小时加急出货

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-400	V
Continuous Drain Current at $T_{amb}=25^{\circ}\text{C}$	I_D	-45	mA
Pulsed Drain Current	I_{DM}	-400	mA
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	P_{tot}	700	mW
Operating and Storage Temperature	T_j, T_{stg}	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-400		V	$I_D=-1\text{mA}, V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-4.5	V	$ID=-1\text{mA}, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}		-20 -2	μA mA	$V_{DS}=-400\text{V}, V_{GS}=0$ $V_{DS}=-320\text{V}, V_{GS}=0\text{V}, T=125^{\circ}\text{C}(2)$
On-State Drain Current(1)	$I_{D(on)}$	-100		mA	$V_{DS}=-25\text{V}, V_{GS}=-10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		150	Ω	$V_{GS}=-10\text{V}, I_D=-50\text{mA}$
Forward Transconductance(1)(2)	g_{fs}	40		mS	$V_{DS}=-25\text{V}, I_D=-50\text{mA}$
Input Capacitance (2)	C_{iss}		120	pF	
Common Source Output Capacitance (2)	C_{oss}		20	pF	$V_{DS}=-25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$
Reverse Transfer Capacitance (2)	C_{rss}		5	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		10	ns	
Rise Time (2)(3)	t_r		15	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		15	ns	
Fall Time (2)(3)	t_f		20	ns	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

